THE DATASHEET OF

BSP19TA

SOT223 NPN SILICON PLA

HIGH VOLTAGE TRANSIS

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FEATURES

- High V_{CEO} – 350V
- Low saturation voltage

COMPLEMENTARY TYPE – BSP16

PARTMARKING DETAIL – BSP19

ABSOLUTE MAXIMUM RATINGS

PARAMETER
Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Peak Pulse Current
Continuous Collector Current
Power Dissipation at T_{amb}=25°C
Operating and Storage Temperature Range

ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	MI
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	40
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	35
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5
Collector Cut-Off Current	I_{CBO}	
Emitter Cut-Off Current	I_{EBO}	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	
Static Forward Current Transfer Ratio	h_{FE}	40 50
Transition Frequency	f_T	70
Output Capacitance	C_{obo}	

*Measured under pulsed conditions. Pulse
Spice parameter data is available upon re
For typical characteristics graphs see FZT6